

Dong-Seok Leem

List of Publications by Year in descending order

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67
papers

2,802
citations

159585

30
h-index

175258

52
g-index

70
all docs

70
docs citations

70
times ranked

3497
citing authors

#	ARTICLE	IF	CITATIONS
1	Efficient Organic Solar Cells with Solution-Processed Silver Nanowire Electrodes. <i>Advanced Materials</i> , 2011, 23, 4371-4375.	21.0	513
2	Amount of retained austenite at room temperature after reverse transformation of martensite to austenite in an Fe-13%Cr-7%Ni-3%Si martensitic stainless steel. <i>Scripta Materialia</i> , 2001, 45, 767-772.	5.2	152
3	Low driving voltage and high stability organic light-emitting diodes with rhenium oxide-doped hole transporting layer. <i>Applied Physics Letters</i> , 2007, 91, 011113.	3.3	138
4	Morphology- and Orientation-Controlled Gallium Arsenide Nanowires on Silicon Substrates. <i>Nano Letters</i> , 2007, 7, 39-44.	9.1	99
5	Organic-on-silicon complementary metal-oxide-semiconductor colour image sensors. <i>Scientific Reports</i> , 2015, 5, 7708.	3.3	94
6	Reduced Graphene Oxide Electrodes for Large Area Organic Electronics. <i>Advanced Materials</i> , 2011, 23, 1558-1562.	21.0	92
7	Investigation of a Conjugated Polyelectrolyte Interlayer for Inverted Polymer:Fullerene Solar Cells. <i>Advanced Energy Materials</i> , 2013, 3, 718-723.	19.5	92
8	Effectiveness of p-dopants in an organic hole transporting material. <i>Applied Physics Letters</i> , 2009, 94, .	3.3	88
9	Green-Sensitive Organic Photodetectors with High Sensitivity and Spectral Selectivity Using Subphthalocyanine Derivatives. <i>ACS Applied Materials & Interfaces</i> , 2013, 5, 13089-13095.	8.0	85
10	Highly efficient tandem p-i-n organic light-emitting diodes adopting a low temperature evaporated rhenium oxide interconnecting layer. <i>Applied Physics Letters</i> , 2008, 93, .	3.3	77
11	Low Resistance and Reflective Mg-Doped Indium Oxide-Ag Ohmic Contacts for Flip-Chip Light-Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , 2004, 16, 1450-1452.	2.5	65
12	High performance top-emitting organic light-emitting diodes with copper iodide-doped hole injection layer. <i>Organic Electronics</i> , 2008, 9, 805-808.	2.6	63
13	Low dark current small molecule organic photodetectors with selective response to green light. <i>Applied Physics Letters</i> , 2013, 103, 043305.	3.3	60
14	Formation of low resistance and transparent ohmic contacts to p-type GaN using Ni-Mg solid solution. <i>Applied Physics Letters</i> , 2003, 83, 3513-3515.	3.3	59
15	Narrow-Band Organic Photodiodes for High-Resolution Imaging. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 26143-26151.	8.0	59
16	Noise and detectivity limits in organic shortwave infrared photodiodes with low disorder. <i>Npj Flexible Electronics</i> , 2020, 4, .	10.7	59
17	Improvement of the luminous intensity of light-emitting diodes by using highly transparent Ag-indium tin oxide p-type ohmic contacts. <i>IEEE Photonics Technology Letters</i> , 2005, 17, 291-293.	2.5	57
18	Effect of host organic semiconductors on electrical doping. <i>Organic Electronics</i> , 2010, 11, 486-489.	2.6	57

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19	Low-resistance and highly-reflective Zn ²⁺ /Ni solid solution/Ag ohmic contacts for flip-chip light-emitting diodes. <i>Applied Physics Letters</i> , 2003, 83, 4990-4992.	3.3	56
20	Enhancement of the light output of GaN-based light-emitting diodes with surface-patterned ITO electrodes by maskless wet-etching. <i>Solid-State Electronics</i> , 2007, 51, 793-796.	1.4	51
21	Solution-processable infrared photodetectors: Materials, device physics, and applications. <i>Materials Science and Engineering Reports</i> , 2021, 146, 100643.	31.8	49
22	Highly efficient orange organic light-emitting diodes using a novel iridium complex with imide group-containing ligands. <i>Journal of Materials Chemistry</i> , 2009, 19, 8824.	6.7	47
23	Dynamic Characterization of Green-Sensitive Organic Photodetectors Using Nonfullerene Small Molecules: Frequency Response Based on the Molecular Structure. <i>Journal of Physical Chemistry C</i> , 2014, 118, 13424-13431.	3.1	42
24	Rubidium-Carbonate-Doped 4,7-Diphenyl-1,10-phenanthroline Electron Transporting Layer for High-Efficiency p-i-n Organic Light Emitting Diodes. <i>Electrochemical and Solid-State Letters</i> , 2009, 12, J8.	2.2	40
25	A high performance green-sensitive organic photodiode comprising a bulk heterojunction of dimethyl-quinacridone and dicyanovinyl terthiophene. <i>Journal of Materials Chemistry C</i> , 2013, 1, 2666.	5.5	40
26	Dipolar donor-acceptor molecules in the cyanine limit for high efficiency green-light-selective organic photodiodes. <i>Journal of Materials Chemistry C</i> , 2016, 4, 1117-1125.	5.5	40
27	Light-output enhancement of GaN-based light-emitting diodes by using hole-patterned transparent indium tin oxide electrodes. <i>Journal of Applied Physics</i> , 2005, 98, 076107.	2.5	33
28	Micron-scale patterning of high conductivity poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate) for organic field-effect transistors. <i>Organic Electronics</i> , 2010, 11, 1307-1312.	2.6	33
29	Organic Upconversion Imager with Dual Electronic and Optical Readouts for Shortwave Infrared Light Detection. <i>Advanced Functional Materials</i> , 2021, 31, 2100565.	14.9	33
30	Electronic and chemical properties of cathode structures using 4,7-diphenyl-1,10-phenanthroline doped with rubidium carbonate as electron injection layers. <i>Journal of Applied Physics</i> , 2009, 105, 113714.	2.5	32
31	High-quality nonalloyed rhodium-based ohmic contacts to p-type GaN. <i>Applied Physics Letters</i> , 2003, 83, 2372-2374.	3.3	30
32	Formation of Nonalloyed Low Resistance Ni/Au Ohmic Contacts to p-Type GaN Using Au Nanodots. <i>Electrochemical and Solid-State Letters</i> , 2004, 7, G179.	2.2	26
33	High efficiency p-i-n top-emitting organic light-emitting diodes with a nearly Lambertian emission pattern. <i>Journal of Applied Physics</i> , 2009, 106, .	2.5	25
34	Spin-coated ultrathin poly(vinylidene fluoride-co-trifluoroethylene) films for flexible and transparent electronics. <i>Journal of Materials Chemistry</i> , 2011, 21, 5057.	6.7	25
35	Low dark current inverted organic photodetectors employing MoO _x /Al cathode interlayer. <i>Organic Electronics</i> , 2015, 24, 176-181.	2.6	21
36	Green-Light-Selective Organic Photodiodes with High Detectivity for CMOS Color Image Sensors. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 51688-51698.	8.0	19

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37	Green-light-selective organic photodiodes for full-color imaging. <i>Optics Express</i> , 2019, 27, 25410.	3.4	19
38	Rapid Patterning of Single-Wall Carbon Nanotubes by Interlayer Lithography. <i>Small</i> , 2010, 6, 2530-2534.	10.0	18
39	Flexible multilayer inverted polymer light-emitting diodes with a gravure contact printed Cs ₂ CO ₃ electron injection layer. <i>Applied Physics Letters</i> , 2011, 98, 103306.	3.3	18
40	Low-resistance and transparent ohmic contacts to p-type GaN using Zn-Ni solid solution/Au scheme. <i>Applied Physics Letters</i> , 2004, 84, 4663-4665.	3.3	16
41	Efficient and colour-stable hybrid white organic light-emitting diodes utilizing electron-hole balanced spacers. <i>Journal Physics D: Applied Physics</i> , 2010, 43, 405102.	2.8	16
42	Formation mechanism of cerium oxide-doped indium oxide/Ag Ohmic contacts on p-type GaN. <i>Applied Physics Letters</i> , 2006, 89, 262115.	3.3	15
43	Low resistance and transparent Ni-La solid solution/Au ohmic contacts to p-type GaN. <i>Applied Physics Letters</i> , 2004, 84, 1504-1506.	3.3	13
44	Low Resistance and Highly Reflective Sb-Doped SnO ₂ /Ag Ohmic Contacts to p-Type GaN for Flip-Chip LEDs. <i>Electrochemical and Solid-State Letters</i> , 2004, 7, G219.	2.2	13
45	Highly Responsive and Thermally Reliable Near-Infrared Organic Photodiodes Utilizing Naphthalocyanine Molecules Tuned with Axial Ligands. <i>Advanced Optical Materials</i> , 2021, 9, 2001682.	7.3	13
46	High Performance Shortwave Infrared Organic Photodetectors Adopting Thiadiazole Quinoxaline-Based Copolymers. <i>Advanced Optical Materials</i> , 2022, 10, .	7.3	13
47	High-Quality Cu-Ni Solid Solution/Ag Ohmic Contacts for Flip-Chip Light-Emitting Diodes. <i>Electrochemical and Solid-State Letters</i> , 2004, 7, G210.	2.2	11
48	Energy Gap between Photoluminescence and Electroluminescence as Recombination Indicator in Organic Small-Molecule Photodiodes. <i>Journal of Physical Chemistry C</i> , 2016, 120, 10176-10184.	3.1	11
49	Nano-dot addition effect on the electrical properties of Ni contacts to p-type GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 2524-2527.	0.8	10
50	Bi-layered metal-oxide thin films processed at low-temperature for the encapsulation of highly stable organic photo-diode. <i>Organic Electronics</i> , 2017, 41, 259-265.	2.6	10
51	Characteristics of Ni-Doped IZO Layers Grown on IZO Anode for Enhancing Hole Injection in OLEDs. <i>Journal of the Electrochemical Society</i> , 2008, 155, J340.	2.9	8
52	Low resistance Ni-Zn solid solution/Pd ohmic contacts to p-type GaN. <i>Semiconductor Science and Technology</i> , 2004, 19, 669-672.	2.0	6
53	GaN-based light-emitting diodes with Ni-Mg solid solution/Au p-type ohmic contact. <i>Solid-State Electronics</i> , 2004, 48, 1597-1600.	1.4	6
54	Low-Resistance and Reflective Ni/Rh and Ni/Au/Rh Contacts to p-GaN for Flip-Chip LEDs. <i>Electrochemical and Solid-State Letters</i> , 2005, 8, G17.	2.2	6

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55	Estimation of the mean emission zone in phosphorescent organic light-emitting diodes with a thin emitting layer. <i>Optics Express</i> , 2010, 18, 16715.	3.4	6
56	Formation of High-Quality Ohmic Contacts to p-GaN for Flip-Chip LEDs Using Ag ^x TiN _x Al. <i>Electrochemical and Solid-State Letters</i> , 2005, 8, G150.	2.2	5
57	Low resistance and highly reflective Cu ^x Ni solid solution/Ag ohmic contacts to p-GaN for flip-chip light emitting diodes. <i>Physica Status Solidi A</i> , 2004, 201, 2823-2826.	1.7	4
58	High transparency of Ag ^x Zn ^x Ni solid ^x solution ohmic contacts for GaN-based ultraviolet light-emitting diodes. <i>Applied Physics Letters</i> , 2005, 86, 102102.	3.3	4
59	Investigations of electron-injection mechanisms and interfacial chemical reactions of Bphen doped with rubidium carbonate in OLEDs. , 2008, , .		3
60	Paper 161: Effectiveness of p-Dopants in an Organic Hole Transporting Material. Digest of Technical Papers SID International Symposium, 2009, 40, 1719-1721.	0.3	2
61	35.1: Invited Paper: Electrical Doping for High Performance Organic Light Emitting Diodes. Digest of Technical Papers SID International Symposium, 2009, 40, 491-494.	0.3	2
62	Formation of Nonalloyed Low Resistance Ni/Au Ohmic Contacts to p-Type GaN Using Au Nanodots [Electrochemical and Solid-State Letters, 7, G179 (2004)]. <i>Electrochemical and Solid-State Letters</i> , 2004, 7, L1.	2.2	1
63	Recent development of patterned structure light-emitting diodes. , 2005, , .		1
64	Gravure contact printing of flexible, high-performance polymer light emitting diodes for large-area displays and lighting. <i>Materials Research Society Symposia Proceedings</i> , 2011, 1340, 1.	0.1	1
65	Formation of high quality ohmic contacts to p-GaN using metal/transparent conducting oxides. , 0, , .		0
66	Low Resistance Ni-Mg Solid Solution/Pt Ohmic Contacts to p-Type GaN. <i>Electrochemical and Solid-State Letters</i> , 2004, 7, G65.	2.2	0
67	Electrical doping for high performance organic light emitting diodes. , 2009, , .		0